

SILICON TRANSISTOR ARRAY

μ PA1456

NPN SILICON POWER TRANSISTOR ARRAY LOW SPEED SWITCHING USE (DARLINGTON TRANSISTOR) INDUSTRIAL USE

DESCRIPTION

The μ PA1456 is NPN silicon epitaxial Darlington Power Transistor Array that built in 4 circuits designed for driving solenoid, relay, lamp and so on.

FEATURES

- · Easy mount by 0.1 inch of terminal interval.
- High hFE for Darlington Transistor.

ORDERING INFORMATION

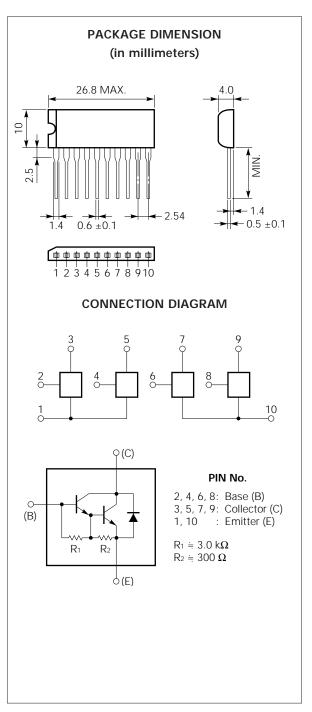
Part Number	Package	Quality Grade	
μ PA 1456H	10 Pin SIP	Standard	

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Vсво	150	V
VCEO	100	V
VEBO	7	V
IC(DC)	±5	A/unit
IC(pulse)*	±10	A/unit
B(DC)	0.5	A/unit
P _{T1} **	3.5	W
P _{T2} ***	28	W
Tj	150	.C
Tstg -55	to +150) .C
	VCEO VEBO IC(DC) IC(pulse)* IB(DC) PT1** PT2*** TJ	VCEO 100 VEBO 7 IC(DC) ±5 IC(pulse)* ±10 IB(DC) 0.5 PT1** 3.5 PT2*** 28 Tj 150

- * PW \leq 300 μ s, Duty Cycle \leq 10 %
- ** 4 Circuits, Ta = 25 °C
- *** 4 Circuits, Tc = 25 °C



The information in this document is subject to change without notice.

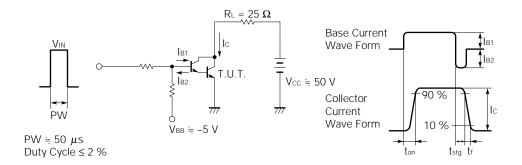


ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS	
Collector Leakage Current	Ісво			10	μΑ	Vcb = 100 V, IE = 0	
Emitter Leakage Current	Іево			10	mA	V _{EB} = 5 V, I _C = 0	
DC Current Gain	h _{FE1} *	2000	7000	20000	_	Vce = 2 V, Ic = 2 A	
DC Current Gain	h _{FE2} *	500	3000		_	Vce = 2 V, Ic = 4 A	
Collector Saturation Voltage	VCE(sat) *		0.9	1.5	V	Ic = 2 A, I _B = 2 mA	
Base Saturation Voltage	V _{BE(sat)} *		1.6	2	V	Ic = 2 A, I _B = 2 mA	
Turn On Time	ton		1		μs	Ic = 2 A	
Storage Time	tstg		3		μs	$I_{B1} = -I_{B2} = 2 \text{ mA}$ $V_{CC} = 50 \text{ V, RL} = 25 \Omega$	
Fall Time	tr		1		μ s See test circuit		

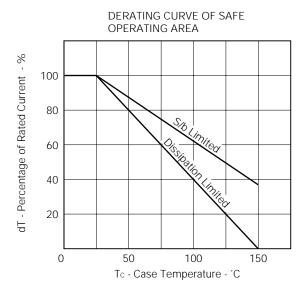
^{*} PW \leq 350 μ s, Duty Cycle \leq 2 % / pulsed

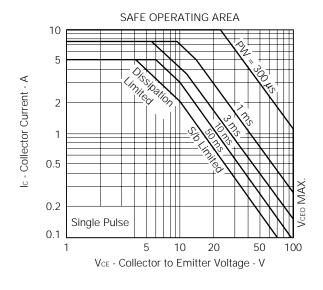
SWITCHING TIME TEST CIRCUIT



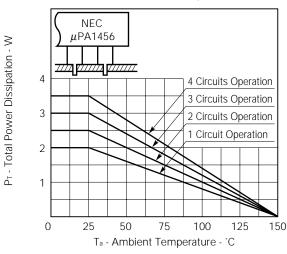


TYPICAL CHARACTERISTICS (Ta = 25 °C)

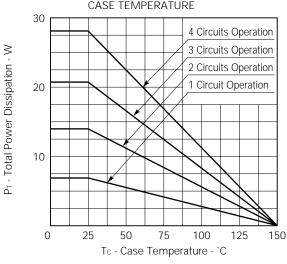




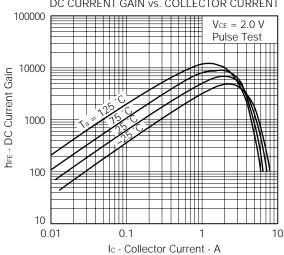




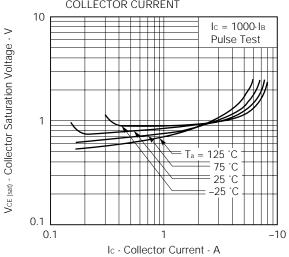




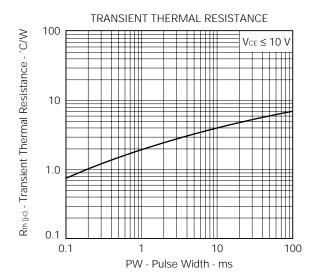
DC CURRENT GAIN vs. COLLECTOR CURRENT

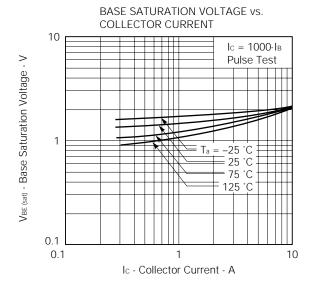


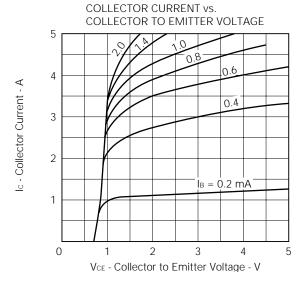
COLLECTOR SATURATION VOLTAGE vs. **COLLECTOR CURRENT**













REFERENCE

Document Name	Document No.
NEC semiconductor device reliability/quality control system.	TEI-1202
Quality grade on NEC semiconductor devices.	IEI-1209
Semiconductor device mounting technology manual.	IEI-1207
Semiconductor device package manual.	IEI-1213
Guide to quality assurance for semiconductor devices.	MEI-1202
Semiconductor selection guide.	MF-1134

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